16 Megabit Concurrent SuperFlash
SST36VF1601 / SST36VF1602

Advance Information

FEATURES:

- **Organized as 1M x16**
- **Dual-Bank Architecture for Concurrent Read/Write Operation**
  - 16 Mbit Bottom Sector Protection
    - SST36VF1601: 12 Mbit + 4 Mbit
  - 16 Mbit Top Sector Protection
    - SST36VF1602: 4 Mbit + 12 Mbit
- **Single 2.7-3.6V Read and Write Operations**
- **Superior Reliability**
  - Endurance: 100,000 Cycles (typical)
  - Greater than 100 years Data Retention
- **Low Power Consumption:**
  - Active Current: 25 mA (typical)
  - Standby Current: 4 µA (typical)
  - Auto Low Power Mode: 4 µA (typical)
- **Hardware Sector Protection/WP# Input Pin**
  - Protects 4 outer most sectors (4 KWord) in the larger bank by driving WP# low and unprotects by driving WP# high
- **Hardware Reset Pin (RESET#)**
  - Resets the internal state machine to reading data array
- **Sector-Erase Capability**
  - Uniform 1 KWord sectors
- **Block-Erase Capability**
  - Uniform 32 KWord blocks
- **Read Access Time**
  - 70 and 90 ns
- **Latched Address and Data**
- **Fast Erase and Word-Program:**
  - Sector-Erase Time: 18 ms (typical)
  - Block-Erase Time: 18 ms (typical)
  - Chip-Erase Time: 70 ms (typical)
  - Word-Program Time: 14 µs (typical)
  - Chip Rewrite Time: 8 seconds (typical)
- **Automatic Write Timing**
  - Internal V_{PP} Generation
- **End-of-Write Detection**
  - Toggle Bit
  - Data# Polling
  - Ready/Busy# pin
- **CMOS I/O Compatibility**
- **Conforms to Common Flash Memory Interface (CFI)**
- **JEDEC Standards**
  - Flash EEPROM Pinouts and command sets
- **Packages Available**
  - 48-Pin TSOP (12mm x 20mm)
  - 48-Ball TFBGA (8mm x 10mm)

PRODUCT DESCRIPTION

The SST36VF1601/1602 are 1M x16 CMOS Concurrent Read/Write Flash Memory manufactured with SST's proprietary, high performance CMOS SuperFlash technology. The split-gate cell design and thick oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches.The SST36VF1601/1602 write (Program or Erase) with a 2.7-3.6V power supply. The SST36VF1601/1602 devices conform to JEDEC standard pinouts for x16 memories.

Featuring high performance Word-Program, the SST36VF1601/1602 devices provide a typical Word-Program time of 14 µsec. The devices use Toggle Bit or Data# Polling to detect the completion of the Program or Erase operation. To protect against inadvertent write, the SST36VF1601/1602 devices have on-chip hardware and Software Data Protection schemes. Designed, manufactured, and tested for a wide spectrum of applications, the SST36VF1601/1602 devices are offered with a guaranteed endurance of 10,000 cycles. Data retention is rated at greater than 100 years.

The SST36VF1601/1602 are suited for applications that require convenient and economical updating of program, configuration, or data memory. For all system applications, the SST36VF1601/1602 significantly improve performance and reliability, while lowering power consumption. The SST36VF1601/1602 inherently use less energy during Erase and Program than alternative flash technologies. The total energy consumed is a function of the applied voltage, current, and time of application. Since for any given voltage range, the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation is less than alternative flash technologies. The SST36VF1601/1602 also improve flexibility while lowering the cost for program, data, and configuration storage applications.

The SuperFlash technology provides fixed Erase and Program times, independent of the number of Erase/Program cycles that have occurred. Therefore the system software or hardware does not have to be modified or de-rated as is necessary with alternative flash technolo-

gies, whose Erase and Program times increase with accumulated Erase/Program cycles.

To meet high density, surface mount requirements, the SST36VF1601/1602 are offered in 48-pin TSOP and 48-ball TFBGA packages. See Figures 3 and 4 for pinouts.

Device Operation

Commands are used to initiate the memory operation functions of the device. Commands are written to the device using standard microprocessor write sequences. A command is written by asserting WE# low while keeping CE# low. The address bus is latched on the falling edge of WE# or CE#, whichever occurs last. The data bus is latched on the rising edge of WE# or CE#, whichever occurs first.

The SST36VF1601/1602 also have the **Auto Low Power** mode which puts the device in a near standby mode after data has been accessed with a valid Read operation. This reduces the I_{DD} active read current to typically 4 µA. The device exits the Auto Low Power mode with any address transition or control signal transition used to initiate another read cycle, with no access time penalty.

Concurrent Read/Write Operation

Dual bank architecture of SST36VF1601/1602 devices allows the Concurrent Read/Write operation whereby the user can read from one bank while program or erase in the other bank. This operation can be used when the user needs to read system code in one bank while updating data in the other bank.

CONCURRENT READ/WRITE STATE TABLE

Bank 1	Bank 2
Read	No Operation
Read	Write
Write	Read
Write	No Operation
No Operation	Read
No Operation	Write

Note: For the purposes of this table, write means to Block-, Sector-, or Chip-Erase, or Word-Program as applicable to the appropriate bank.

Read

The Read operation of the SST36VF1601/1602 is controlled by CE# and OE#, both have to be low for the system to obtain data from the outputs. CE# is used for device selection. When CE# is high, the chip is deselected and only standby power is consumed. OE# is the output control and is used to gate data from the output pins. The data bus is in high impedance state when either CE# or OE# is high. Refer to the Read cycle timing diagram for further details (Figure 5).

Word-Program Operation

The SST36VF1601/1602 are programmed on a word-by-word basis. The Program operation consists of three steps. The first step is the three-byte load sequence for Software Data Protection. The second step is to load word address and word data. During the Word-Program operation, the addresses are latched on the falling edge of either CE# or WE#, whichever occurs last. The data is latched on the rising edge of either CE# or WE#, whichever occurs first. The third step is the internal Program operation which is initiated after the rising edge of the fourth WE# or CE#, whichever occurs first. The Program operation, once initiated, will be completed within 10 µs. See Figures 6 and 7 for WE# and CE# controlled Program operation timing diagrams and Figure 19 for flowcharts. During the Program operation, the only valid reads are Data# Polling and Toggle Bit. During the internal Program operation, the host is free to perform additional tasks. Any commands issued during the internal Program operation are ignored.

Sector- (Block-) Erase Operation

The Sector- (Block-) Erase operation allows the system to erase the device on a sector-by-sector (or block-by-block) basis. The SST36VF1601/1602 offer both Sector-Erase and Block-Erase mode. The sector architecture is based on uniform sector size of 1 KWord. The Block-Erase mode is based on uniform block size of 32 KWord. The Sector-Erase operation is initiated by executing a six-byte command sequence with Sector-Erase command (30H) and sector address (SA) in the last bus cycle. The Block-Erase operation is initiated by executing a six-byte command sequence with Block-Erase command (50H) and block address (BA) in the last bus cycle. The sector or block address is latched on the falling edge of the sixth WE# pulse, while the command (30H or 50H) is latched on the rising edge of the sixth WE# pulse. The internal Erase operation begins after the sixth WE# pulse. See Figures 11 and 12 for timing waveforms. Any commands issued during the Sector- or Block-Erase operation are ignored.

Chip-Erase Operation

The SST36VF1601/1602 provide a Chip-Erase operation, which allows the user to erase all unprotected sectors/blocks to the "1" state. This is useful when the device must be quickly erased.

The Chip-Erase operation is initiated by executing a six-byte command sequence with Chip-Erase command (10H) at address 5555H in the last byte sequence. The Erase operation begins with the rising edge of the sixth WE# or

CE#, whichever occurs first. During the Erase operation, the only valid read is Toggle Bits or Data# Polling. See Table 4 for the command sequence, Figure 10 for timing diagram, and Figure 22 for the flowchart. Any commands issued during the Chip-Erase operation are ignored.

Write Operation Status Detection

The SST36VF1601/1602 provide one hardware and two software means to detect the completion of a Write (Program or Erase) cycle, in order to optimize the system write cycle time. The hadware detection uses the Ready/Busy# (RY/BY#) output pin. The software detection includes two status bits: Data# Polling (DQ_7) and Toggle Bit (DQ_6). The End-of-Write detection mode is enabled after the rising edge of WE#, which initiates the internal Program or Erase operation.

The actual completion of the nonvolatile write is asynchronous with the system; therefore, either a Ready/Busy# (RY/BY#), a Data# Polling (DQ_7) or Toggle Bit (DQ_6) read may be simultaneous with the completion of the Write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either DQ_7 or DQ_6. In order to prevent spurious rejection, if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both reads are valid, then the device has completed the write cycle, otherwise the rejection is valid.

Ready/Busy# (RY/BY#)

The SST36VF1601/1602 includes a Ready/Busy# (RY/BY#) output signal. During any SDP initiated operation, e.g., Erase, Program, CFI or ID Read operation, RY/BY# is actively pulled low, indicating a SDP controlled operation is in Progress. The status of RY/BY# is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-, Block- or Bank-Erase, the RY/BY# is valid after the rising edge of sixth WE# or (CE#) pulse. RY/BY# is an open drain output that allows several devices to be tied in parallel to V_{DD} via an external pull up resistor. Ready/Busy# is in high impedance whenever OE# or CE# is high or RST# is low.

Data# Polling (DQ_7)

When the SST36VF1601/1602 are in the internal Program operation, any attempt to read DQ_7 will produce the complement of the true data. Once the Program operation is completed, DQ_7 will produce true data. The device is then ready for the next operation. During internal Erase operation, any attempt to read DQ_7 will produce a '0'. Once the internal Erase operation is completed, DQ_7 will produce a '1'. The Data# Polling (DQ_7) is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-, Block- or Chip-Erase, the Data# Polling (DQ_7) is valid after the rising edge of sixth WE# (or CE#) pulse. See Figure 8 for Data# Polling (DQ_7) timing diagram and Figure 20 for a flowchart.

Toggle Bits (DQ_6 and DQ_2)

During the internal Program or Erase operation, any consecutive attempts to read DQ_6 will produce alternating 1's and 0's, i.e., toggling between 1 and 0. When the internal Program or Erase operation is completed, the DQ_6 bit will stop toggling. The device is then ready for the next operation. The Toggle Bit (DQ_6) is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-, Block- or Chip-Erase, the Toggle Bit (DQ_6) is valid after the rising edge of sixth WE# (or CE#) pulse. See Figure 9 for Toggle Bit timing diagram and Figure 21 for a flowchart.

Data Protection

The SST36VF1601/1602 provide both hardware and software features to protect nonvolatile data from inadvertent writes.

Hardware Data Protection

Noise/Glitch Protection: A WE# or CE# pulse of less than 5 ns will not initiate a write cycle.

V_{DD} Power Up/Down Detection: The Write operation is inhibited when V_{DD} is less than 1.5V.

Write Inhibit Mode: Forcing OE# low, CE# high, or WE# high will inhibit the Write operation. This prevents inadvertent writes during power-up or power-down.

Hardware Block Protection

The SST36VF1601/1602 provide a hardware block protection which protects the outermost 4 KWords in the larger bank.The block is protected when WP# is held low. See Figures 1 and 2 for Block-Protection location.

A user can disable block protection by driving WP# high thus allowing erase or program of data into the protected sectors. WP# must be held high prior to issuing the write command and remain stable until after the entire write operation has completed.

Hardware Reset (RESET#)

When the RESET# input pin is held low for at least T_{RP}, any in progress operation will terminate and return to Read mode. If the part is not busy, a minimum period of T_{RHR} is required after RESET# is driven high before a valid read can take place. If the part is busy, poll RY/BY#, Data# Polling, or Toggle Bit to determine when the device is ready.

Initiating a reset during a Write operation (Program or Erase) is not recommended. Data may be in an undetermined state.

Software Data Protection (SDP)

The SST36VF1601/1602 provide the JEDEC standard Software Data Protection scheme for all data alteration operations, i.e., Program and Erase. Any Program operation requires the inclusion of the three-byte sequence. The three-byte load sequence is used to initiate the Program operation, providing optimal protection from inadvertent Write operations, e.g., during the system power-up or power-down. Any Erase operation requires the inclusion of six-byte sequence. The SST36VF1601/1602 are shipped with the Software Data Protection permanently enabled. See Table 4 for the specific software command codes. During SDP command sequence, invalid commands will abort the device to Read mode within T_{RC}. The contents of DQ_{15}-DQ_8 are "Don't Care" during any SDP command sequence.

Common Flash Memory Interface (CFI)

The SST36VF1601/1602 also contain the CFI information to describe the characteristics of the device. In order to enter the CFI Query mode, the system must write three-byte sequence, same as Software ID Entry command with 98H (CFI Query command) to address 555H in the last byte sequence. Once the device enters the CFI Query mode, the system can read CFI data at the addresses given in Tables 5 through 7. The system must write the CFI Exit command to return to Read mode from the CFI Query mode.

Product Identification

The Product Identification mode identifies the devices and manufacturer. For details, see Table 4 for software operation, Figure 13 for the Software ID Entry and Read timing diagram and Figure 21 for the Software ID Entry command sequence flowchart.

TABLE 1: PRODUCT IDENTIFICATION

	WORD	DATA
Manufacturers ID	0000 H	00BF H
Device ID SST36VF1601	0001 H	2761 H
Device ID SST36VF1602	0001 H	2762 H

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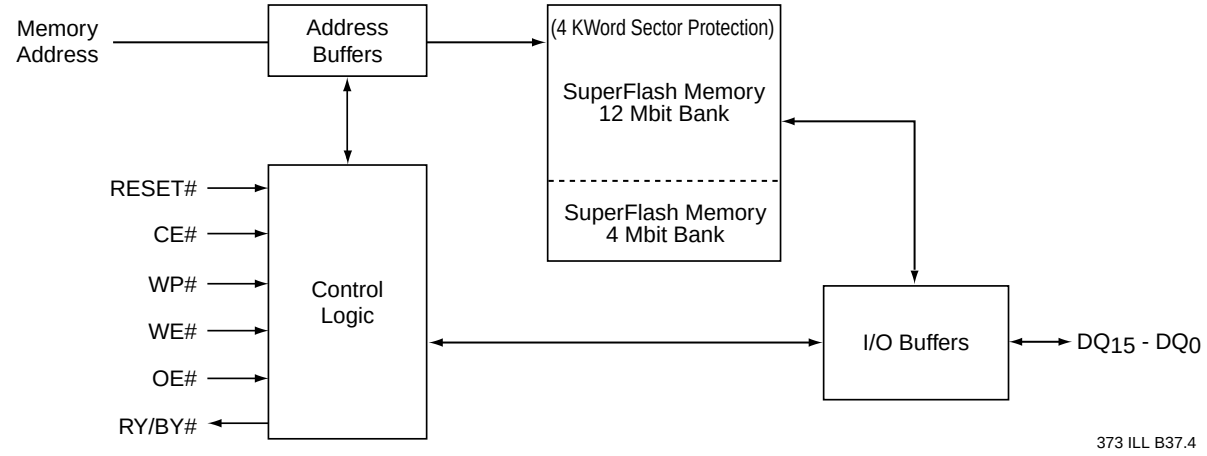
Product Identification Mode Exit/CFI Mode Exit

In order to return to the standard Read mode, the Software Product Identification mode must be exited. Exit is accomplished by issuing the Software ID Exit command sequence, which returns the device to the Read mode. This command may also be used to reset the device to the Read mode after any inadvertent transient condition that apparently causes the device to behave abnormally, e.g., not read correctly. Please note that the Software ID Exit/CFI Exit command is ignored during an internal Program or Erase operation. See Table 4 for software command codes, Figure 15 for timing waveform and Figure 21 for a flowchart.

FUNCTIONAL BLOCK DIAGRAM



Bottom Sector Protection; 32 KWord Blocks; 1 KWord Sectors

FFFFFH F8000H	Block 31	Bank 2
F7FFFH F0000H	Block 30	
EFFFFH E8000H	Block 29	
E7FFFH E0000H	Block 28	
DFFFFH D8000H	Block 27	
D7FFFH D0000H	Block 26	
CFFFFH C8000H	Block 25	
C7FFFH C0000H	Block 24	
BFFFFH B8000H	Block 23	Bank 1
B7FFFH B0000H	Block 22	
AFFFFH A8000H	Block 21	
A7FFFH A0000H	Block 20	
9FFFFH 98000H	Block 19	
97FFFH 90000H	Block 18	
8FFFFH 88000H	Block 17	
87FFFH 80000H	Block 16	
7FFFFH 78000H	Block 15	
77FFFH 70000H	Block 14	
6FFFFH 68000H	Block 13	
67FFFH 60000H	Block 12	
5FFFFH 58000H	Block 11	
57FFFH 50000H	Block 10	
4FFFFH 48000H	Block 9	
47FFFH 40000H	Block 8	
3FFFFH 38000H	Block 7	
37FFFH 30000H	Block 6	
2FFFFH 28000H	Block 5	
27FFFH 20000H	Block 4	
1FFFFH 18000H	Block 3	
17FFFH 10000H	Block 2	
00FFFFH 008000H	Block 1	
007FFFH 001000H	Block 0	
000FFFH 000000H		

4 KWord Sector Protection
(4- 1 KWord Sectors)

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FIGURE 1: SST36VF1601, 1 MEGABIT X16 CONCURRENT SUPERFLASH DUAL-BANK MEMORY ORGANIZATION

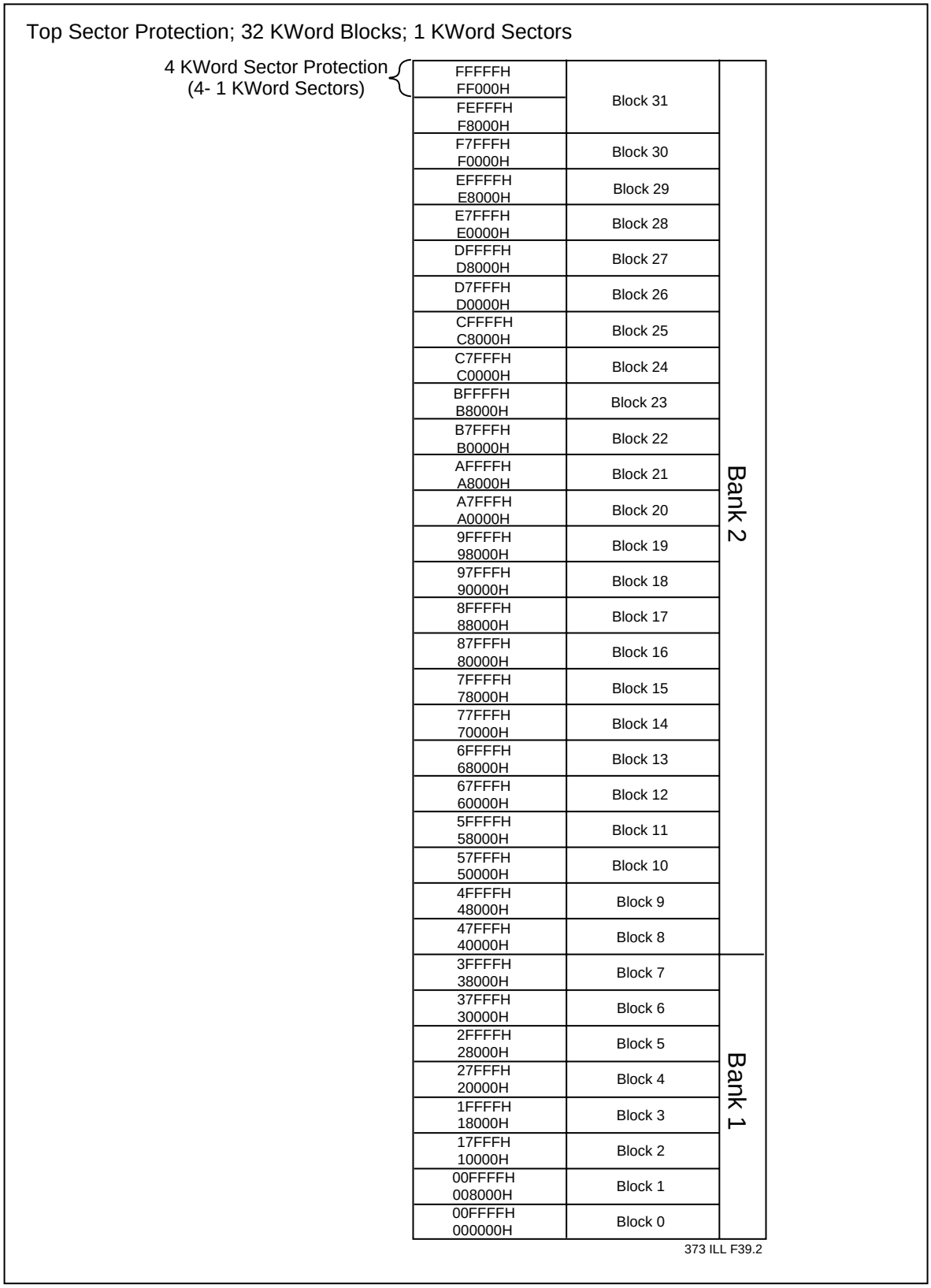

FIGURE 2: SST36VF1602, 1 MEGABIT X16 CONCURRENT SUPERFLASH DUAL-BANK MEMORY ORGANIZATION

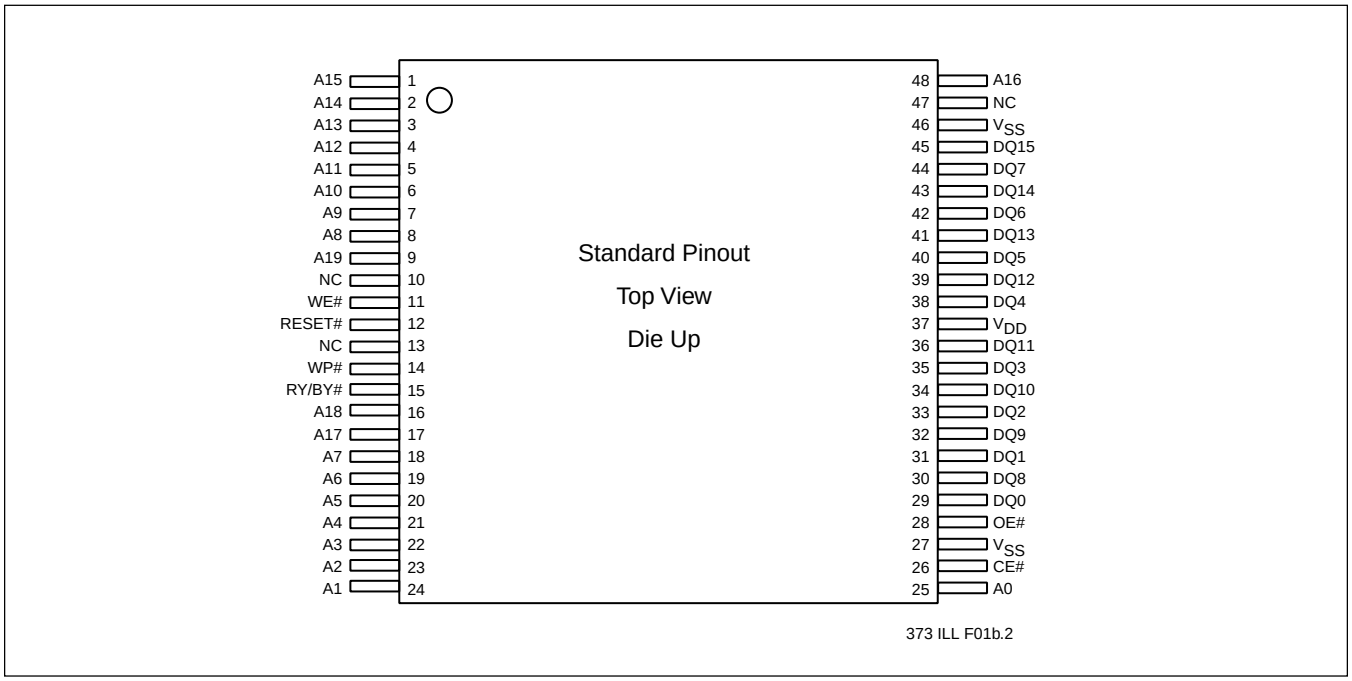

FIGURE 3: PIN ASSIGNMENTS FOR 48-PIN TSOP (12MM X 20MM)

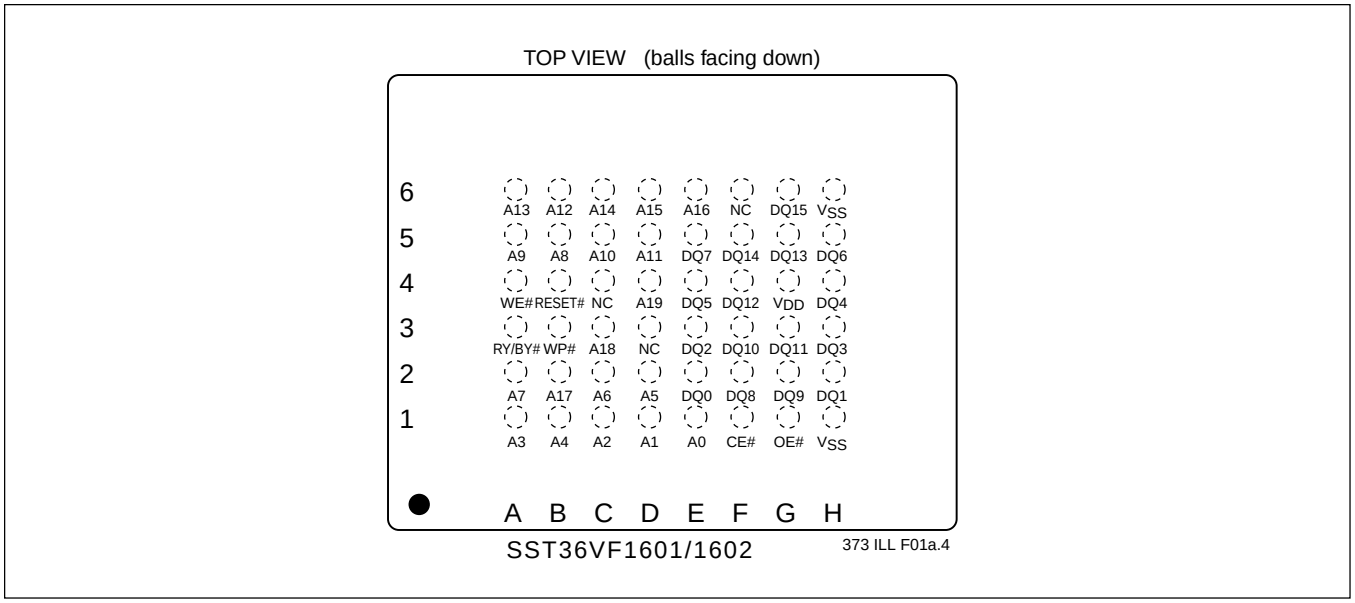

FIGURE 4: PIN ASSIGNMENTS FOR 48-BALL TFBGA (8MM X 10MM)

TABLE 2: PIN DESCRIPTION

Symbol	Pin Name	Functions
A_{19}-A_0	Address Inputs	To provide memory addresses. During Sector-Erase and Hardware Sector Protection A_{19}-A_{11} address lines will select the sector. During Block-Erase A_{19}-A_{15} address lines will select the block.
DQ_{15}-DQ_0	Data Input/output	To output data during read cycles and receive input data during write cycles. Data is internally latched during a Write cycle. The outputs are in tri-state when OE# or CE# is high.
CE#	Chip Enable	To activate the device when CE# is low.
OE#	Output Enable	To gate the data output buffers.
WE#	Write Enable	To control the Write operations.
RESET#	Reset	To reset and return the device to Read mode.
RY/BY#	Ready/Busy#	To output the status of a Program or Erase operation. RY/BY# is an open drain output, so a 10KΩ - 100KΩ pull-up resistor is required to allow RY/BY# to transition high indicating the device is ready to read.
WP#	Write Protect	To protect and unprotect top or bottom 4 sectors from Erase or Program operation.
V_{DD}	Power Supply	To provide 2.7-3.6V power supply voltage
Vss	Ground	
NC	No Connection	Unconnected pins.

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TABLE 3: OPERATION MODES SELECTION

Mode	CE#	OE#	WE#	DQ	Address
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}	A_{IN}
Program	V_{IL}	V_{IH}	V_{IL}	D_{IN}	A_{IN}
Erase	V_{IL}	V_{IH}	V_{IL}	X	Sector or block address, XXH for Chip-Erase
Standby	V_{IH}	X	X	High Z	X
Write Inhibit	X	V_{IL}	X	High Z/ D_{OUT}	X
	X	X	V_{IH}	High Z/ D_{OUT}	X
Product Identification					
					A_{19} - A_1 = V_{IL}, A_0 = V_{IL}
				Manufacturer ID (00BF)	A_{19} - A_1 = V_{IL}, A_0 = V_{IH}
Software Mode	V_{IL}	V_{IL}	V_{IH}	Device ID[1]	See Table 4

Note 1. Device ID = 2761H for SST36VF1601 and 2762H for SST36VF1602

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TABLE 4: SOFTWARE COMMAND SEQUENCE

Command Sequence	1st Bus Write Cycle		2nd Bus Write Cycle		3rd Bus Write Cycle		4th Bus Write Cycle		5th Bus Write Cycle		6th Bus Write Cycle	
	Addr[1]	Data[5]	Addr[1]	Data[5]	Addr[1]	Data[5]	Addr[1]	Data[5]	Addr[1]	Data[5]	Addr[1]	Data[5]
Word-Program	5555H	AAH	2AAAH	55H	5555H	A0H	WA[3]	Data				
Sector-Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	SA_x[2]	30H
Block-Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	BA_x[2]	50H
Chip-Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	5555H	10H
Software ID Entry[6,7]	5555H	AAH	2AAAH	55H	5555H	90H						
CFI Query Entry	5555H	AAH	2AAAH	55H	5555H	98H						
Software ID Exit/ CFI Exit[4]	XXH	F0H										
Software ID Exit/ CFI Exit[4]	5555H	AAH	2AAAH	55H	5555H	F0H						

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Notes: 1. Address format A_{14}-A_0 (Hex),
Address A_{15}-A_{19} are "Don't Care" for Command sequence for SST36VF1601/1602

2. SA_x for Sector-Erase; uses A_{19}-A_{11} address lines
BA_x, for Block-Erase; uses A_{19}-A_{15} address lines

3. WA = Program word address

4. Both Software ID Exit/CFI Exit operations are equivalent

5. DQ_{15} - DQ_8 are "Don't Care" for Command sequence

6. With A_{19} -A_1 =0; SST Manufacturer ID = 00BFH, is read with A_0 = 0,
SST36VF1601 Device ID = 2761H, is read with A_0 = 1.
SST36VF1602 Device ID = 2762H, is read with A_0 = 1.

7. The device does not remain in Software Product Identification Mode if powered down.

TABLE 5: CFI QUERY IDENTIFICATION STRING[1]

Address	Data	Data
10H 11H 12H	0051H 0052H 0059H	Query Unique ASCII string “QRY”
13H 14H	0001H 0007H	Primary OEM command set
15H 16H	0000H 0000H	Address for Primary Extended Table
17H 18H	0000H 0000H	Alternate OEM command set (00H = none exists)
19H 1AH	0000H 0000H	Address for Alternate OEM extended Table (00H = none exits)

Note 1: Refer to CFI publication 100 for more details.

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TABLE 6: SYSTEM INTERFACE INFORMATION

Address	Data	Data
1BH	0027H	V_{DD} Min. (Program/Erase) DQ7-DQ4: Volts, DQ_3-DQ_0: 100 millivolts
1CH	0036H	V_{DD} Max. (Program/Erase) DQ7-DQ4: Volts, DQ_3-DQ_0: 100 millivolts
1DH	0000H	V_{PP} min. (00H = no V_{PP} pin)
1EH	0000H	V_{PP} max. (00H = no V_{PP} pin)
1FH	0004H	Typical time out for Word-Program 2^N µs (2^4 = 16 µs)
20H	0000H	Typical time out for min. size buffer program 2^N µs (00H = not supported)
21H	0004H	Typical time out for individual Sector/Block-Erase 2^N ms (2^4 = 16 ms)
22H	0006H	Typical time out for Chip-Erase 2^N ms (2^6 = 64 ms)
23H	0001H	Maximum time out for Word-Program 2^N times typical (2^1 x 2^4 = 32 µs)
24H	0000H	Maximum time out for buffer program 2^N times typical
25H	0001H	Maximum time out for individual Sector/Block-Erase 2^N times typical (2^1 x 2^4 = 32 ms)
26H	0001H	Maximum time out for Chip-Erase 2^N times typical (2^1 x 2^6 = 128 ms)

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TABLE 7: DEVICE GEOMETRY INFORMATION

Address	Data	Data
27H	0015H	Device size = 2^N Byte (15H = 21; 2^{21} = 2M Bytes)
28H 29H	0001H 0000H	Flash Device Interface description; 0001H = x16-only asynchronous interface
2AH 2BH	0000H 0000H	Maximum number of byte in multi-byte write = 2^N (00H = not supported)
2CH	0002H	Number of Erase Sector/Block sizes supported by device
2DH 2EH 2FH 30H	00FFH 0003H 0008H 0000H	Sector Information (y + 1 = Number of sectors; z x 256B = sector size) y = 1023 + 1 = 1024 sectors (03FFH = 1023) z = 8 x 256 Bytes = 2 KBytes/sector (0008H = 8)
31H 32H 33H 34H	001FH 0000H 0000H 0001H	Block Information (y + 1 = Number of blocks; z x 256B = block size) y = 31 + 1 = 32 blocks (001FH = 31) z = 256 x 256 Bytes = 64 KBytes/block (0100H = 256)

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Advance Information

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias ..... -55°C to +125°C
Storage Temperature ..... -65°C to +150°C
D. C. Voltage on Any Pin to Ground Potential ..... -0.5V to V_{DD} + 0.5V
Transient Voltage (<20 ns) on Any Pin to Ground Potential ..... -1.0V to V_{DD} + 1.0V
Package Power Dissipation Capability (Ta = 25°C) 1.0W
Surface Mount Lead Soldering Temperature (3 Seconds) ..... 240°C
Output Short Circuit Current ..... 50 mA

OPERATING RANGE

Range	Ambient Temp	V_{DD}
Commercial	0 °C to +70 °C	2.7-3.6V
Extended	-20 °C to +85 °C	2.7-3.6V

AC CONDITIONS OF TEST

Input Rise/Fall Time ..... 5 ns
Output Load ..... C_L = 30 pF
See Figures 16 and 17

TABLE 8: DC OPERATING CHARACTERISTICS V_{DD} = 2.7-3.6V

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I_{DD}	Power Supply Current				CE#=OE#=V_{IL},WE#=V_{IH} , all I/Os open, Address input = V_{IL}/V_{IH}, at f=1/T_{RC} Min. CE#=WE#=V_{IL}, OE#=V_{IH}, V_{DD}=V_{DD} Max.
	Read		35	mA	
	Program and Erase		40	mA	
	Concurrent		75	mA	
I_{SB}	Standby V_{DD} Current		20	µA	CE#=V_{IHC}, V_{DD} = V_{DD} Max.
I_{ALP}	Auto Low Power Current		20	µA	CE#=V_{ILC}, V_{DD} = V_{DD} Max., all inputs = V_{IHC} or V_{ILC}, WE# = V_{IHC}
I_{RT}	Reset V_{DD} Current		20	µA	RESET# = V_{SS} ± 0.3V
I_{LI}	Input Leakage Current		1	µA	V_{IN} =GND to V_{DD}, V_{DD} = V_{DD} Max.
I_{LO}	Output Leakage Current		1	µA	V_{OUT} =GND to V_{DD}, V_{DD} = V_{DD} Max.
V_{IL}	Input Low Voltage		0.8	V	V_{DD} = V_{DD} Min.
V_{ILC}	Input Low Voltage (CMOS)		0.3	V	V_{DD} = V_{DD} Max.
V_{IH}	Input High Voltage	0.7 V_{DD}		V	V_{DD} = V_{DD} Max.
V_{IHC}	Input High Voltage (CMOS)	V_{DD}-0.3		V	V_{DD} = V_{DD} Max.
V_{OL}	Output Low Voltage		0.2	V	I_{OL} = 100 µA, V_{DD} = V_{DD} Min.
V_{OH}	Output High Voltage	V_{DD}-0.2		V	I_{OH} = -100 µA, V_{DD} = V_{DD} Min.

373 PGM T8.2

TABLE 9: RECOMMENDED SYSTEM POWER-UP TIMINGS

Symbol	Parameter	Minimum	Units
$T_{PU-READ}$	Power-up to Read Operation	100	µs
$T_{PU-WRITE}$	Power-up to Write Operation	100	µs

373 PGM T9.1

TABLE 10: CAPACITANCE (Ta = 25 °C, f=1 Mhz, other pins open)

Parameter	Description	Test Condition	Maximum
$C_{I/O}$[1]	I/O Pin Capacitance	$V_{I/O}$ = 0V	12 pF
C_{IN}[1]	Input Capacitance	V_{IN} = 0V	6 pF

373 PGM T10.0

TABLE 11: RELIABILITY CHARACTERISTICS

Symbol	Parameter	Minimum Specification	Units	Test Method
N_{END}[1]	Endurance - Flash	10,000	Cycles	JEDEC Standard A117
T_{DR}[1]	Data Retention	100	Years	JEDEC Standard A103
V_{ZAP_HBM}[1]	ESD Susceptibility Human Body Model	2000	Volts	JEDEC Standard A114
V_{ZAP_MM}[1]	ESD Susceptibility Machine Model	200	Volts	JEDEC Standard A115
I_{LTH}[1]	Latch Up	100 + I_{DD}	mA	JEDEC Standard 78

373 PGM T11.0

Note: 1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

Advance Information

AC CHARACTERISTICS

TABLE 12: READ CYCLE TIMING PARAMETERS V_{DD} = 2.7-3.6V

Symbol	Parameter	SST36VF1601/1602-70		SST36VF1601/1602-90		Units
		Min	Max	Min	Max	
T_{RC}	Read Cycle Time	70		90		ns
T_{CE}	Chip Enable Access Time		70		90	ns
T_{AA}	Address Access Time		70		90	ns
T_{OE}	Output Enable Access Time		35		45	ns
T_{CLZ}[1]	CE# Low to Active Output	0		0		ns
T_{OLZ}[1]	OE# Low to Active Output	0		0		ns
T_{CHZ}[1]	CE# High to High-Z Output		20		30	ns
T_{OHZ}[1]	OE# High to High-Z Output		20		30	ns
T_{OH}[1]	Output Hold from Address Change	0		0		ns
T_{RP}[1]	RESET# Pulse Width	500		500		ns
T_{RHR}[1]	RESET# High before Read	50		50		ns
T_{RY}[1,2]	RESET# Pin Low to Read Mode		20		20	µs

373PGM T12.3

TABLE 13: PROGRAM/ERASE CYCLE TIMING PARAMETERS

Symbol	Parameter	Min	Max	Units
T_{BP}	Word-Program Time		20	µs
T_{AS}	Address Setup Time	0		ns
T_{AH}	Address Hold Time	40		ns
T_{CS}	WE# and CE# Setup Time	0		ns
T_{CH}	WE# and CE# Hold Time	0		ns
T_{OES}	OE# High Setup Time	0		ns
T_{OEH}	OE# High Hold Time	10		ns
T_{CP}	CE# Pulse Width	40		ns
T_{WP}	WE# Pulse Width	40		ns
T_{WPH}[1]	WE# Pulse Width High	30		ns
T_{CPH}[1]	CE# Pulse Width High	30		ns
T_{DS}	Data Setup Time	30		ns
T_{DH}[1]	Data Hold Time	0		ns
T_{IDA}[1]	Software ID Access and Exit Time		150	ns
T_{SE}	Sector-Erase		25	ms
T_{BE}	Block-Erase		25	ms
T_{SCE}	Chip-Erase		100	ms
T_{BY}[1]	RY/BY# Delay Time	90		ns
T_{RB}[1]	RY/BY# Recovery Time	0		ns

373PGM T13.3

Note: 1. This parameter is measured only for initial qualification and after the design or process change that could affect this parameter.
2. This parameter applies to Sector-Erase, Block-Erase and Program operations. This parameter does not apply to Chip-Erase.

TIMING DIAGRAMS Address and data format are in HEX.

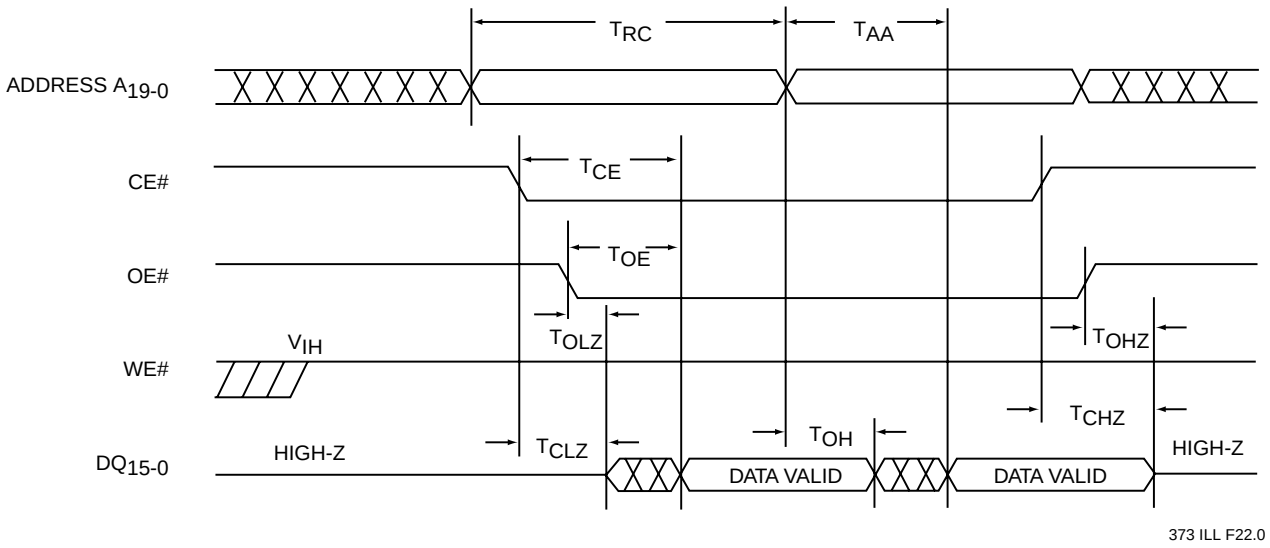


FIGURE 5: READ CYCLE TIMING DIAGRAM

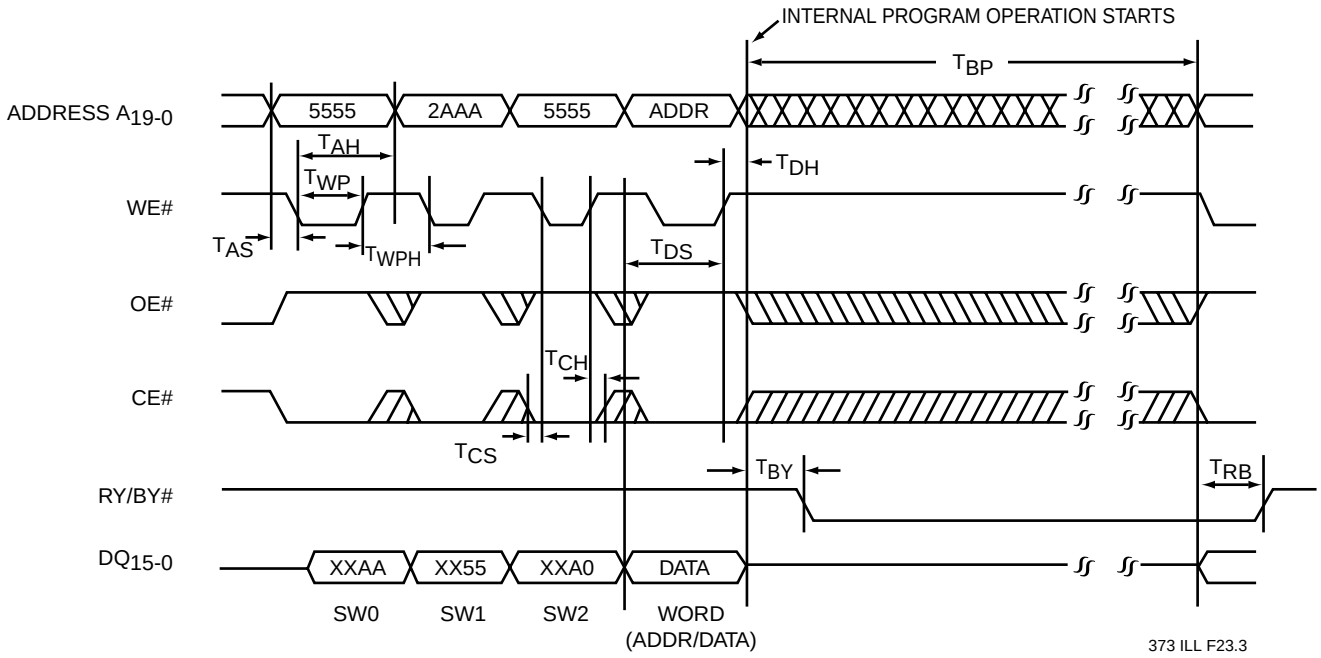


FIGURE 6: WE# CONTROLLED WORD-PROGRAM CYCLE TIMING DIAGRAM

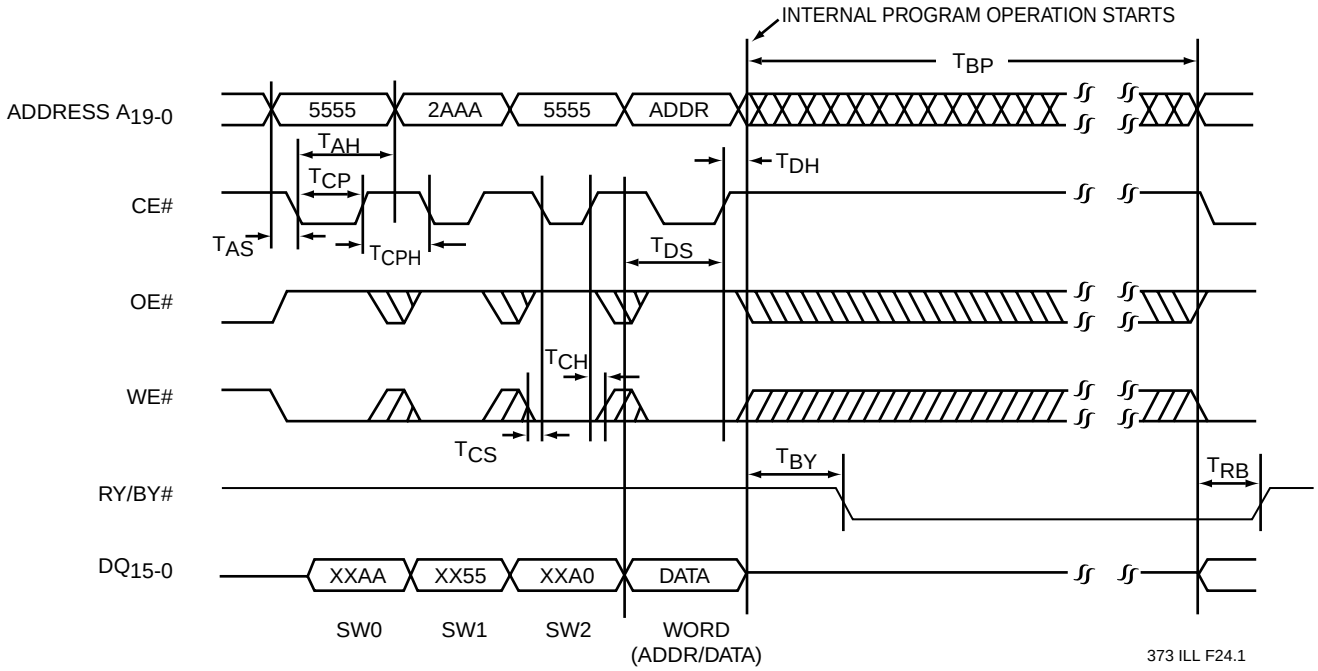


FIGURE 7: CE# CONTROLLED WORD-PROGRAM CYCLE TIMING DIAGRAM

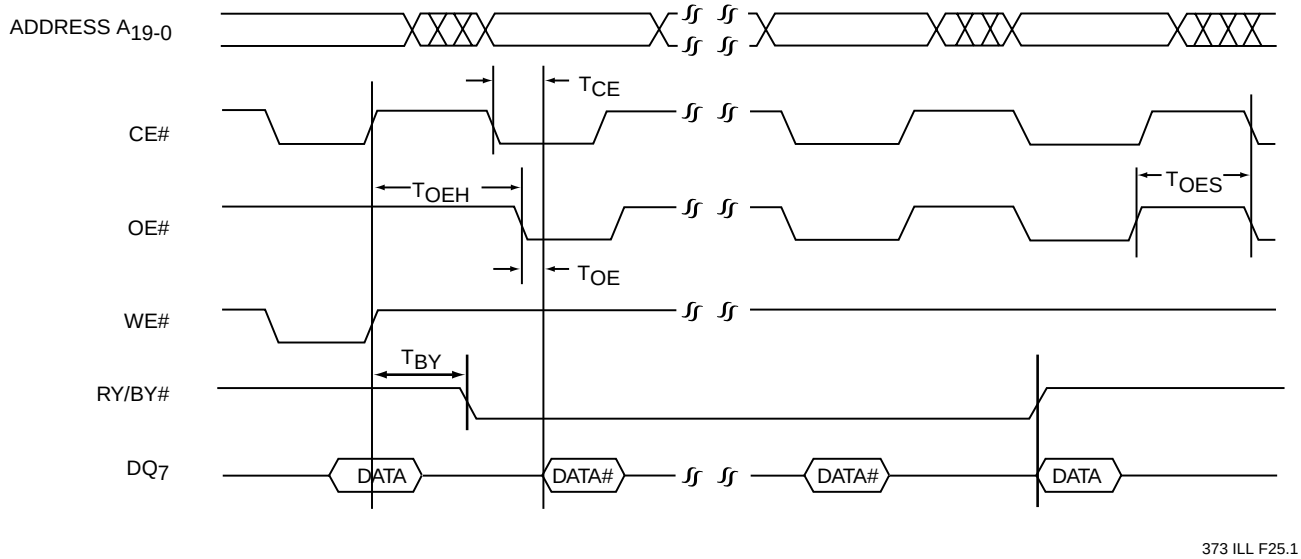


FIGURE 8: DATA# POLLING TIMING DIAGRAM

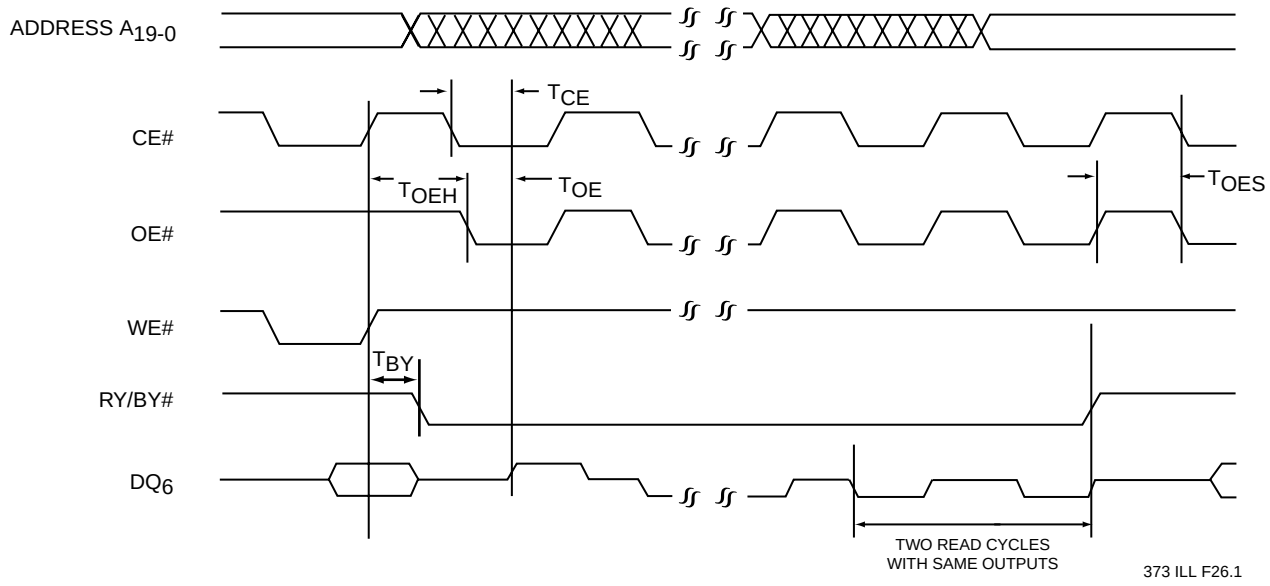
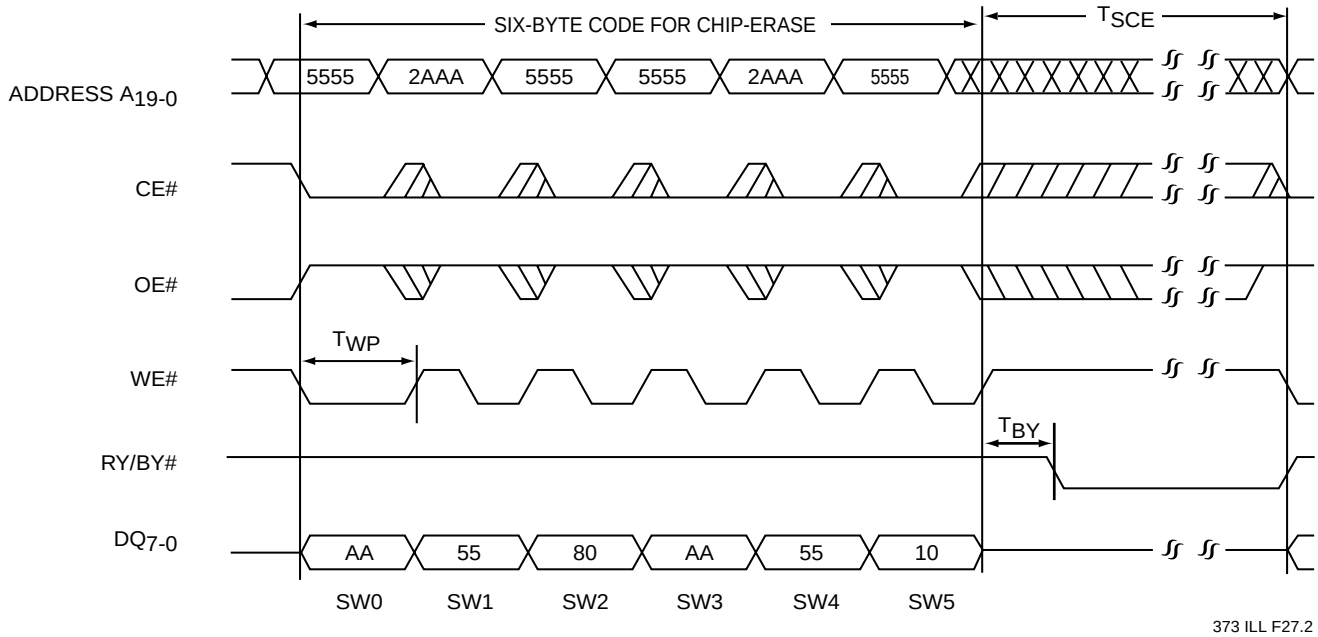
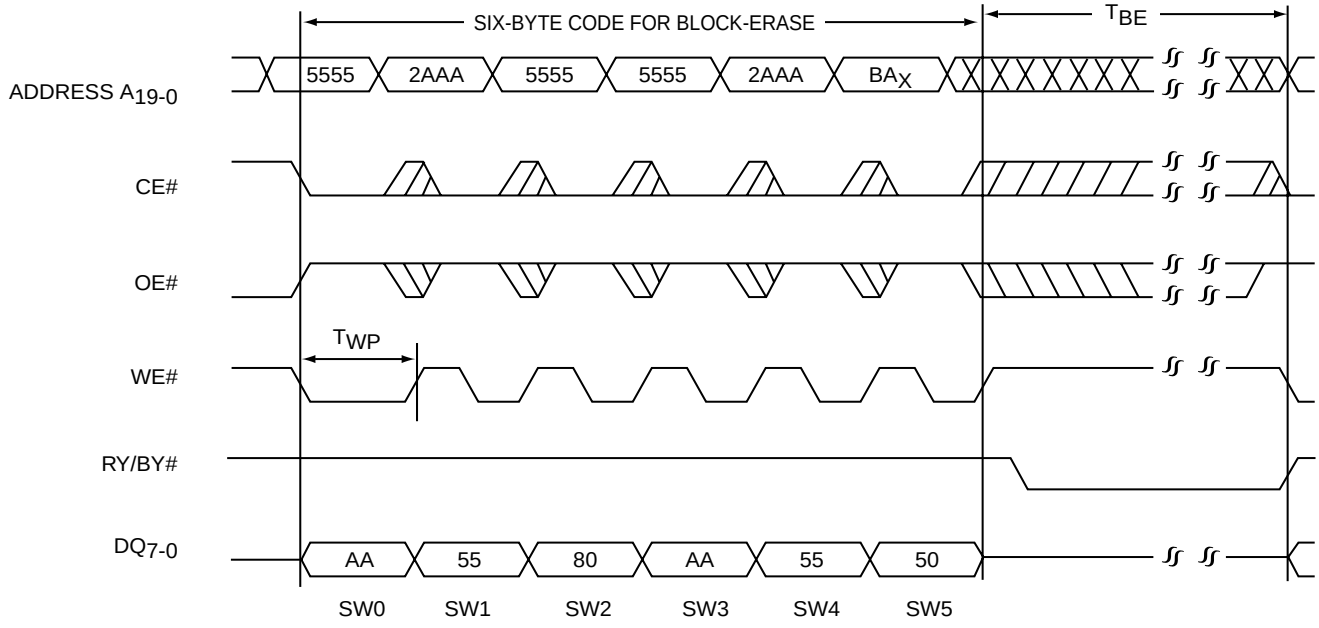


FIGURE 9: TOGGLE BIT TIMING DIAGRAM



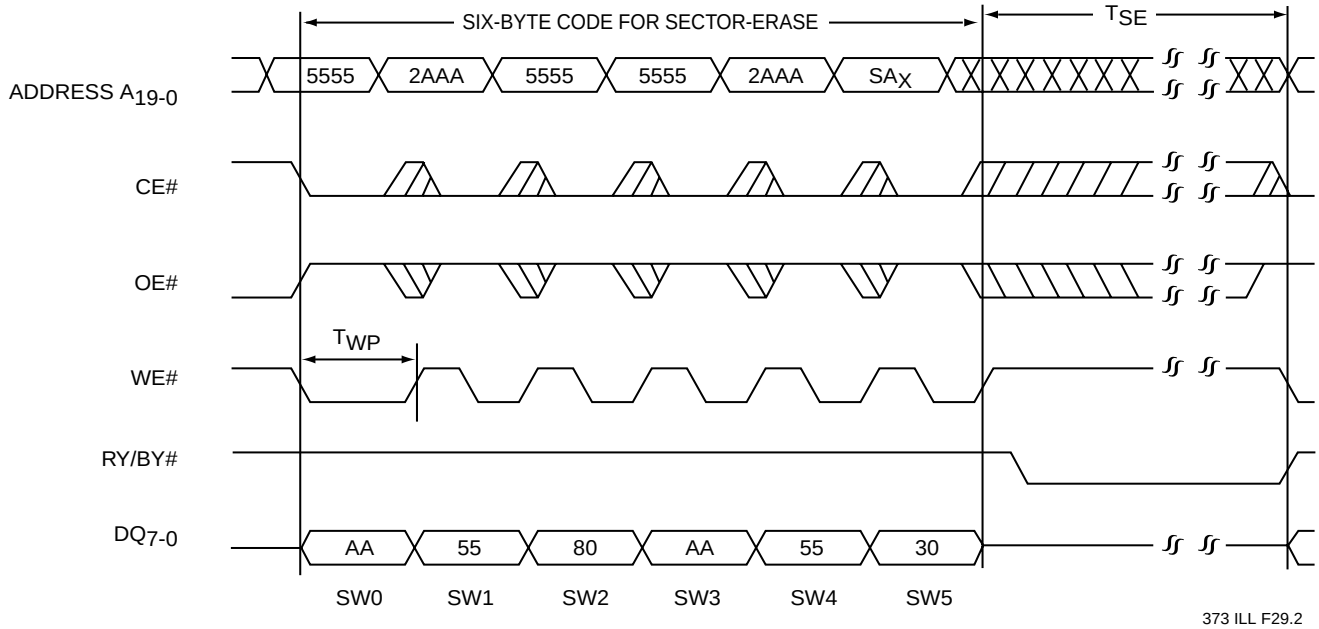
Note: This device also supports CE# controlled Chip-Erase operation. The WE# and CE# signals are interchageable as long as minimum timings are met. (See Table 13)

FIGURE 10: WE# CONTROLLED CHIP-ERASE TIMING DIAGRAM



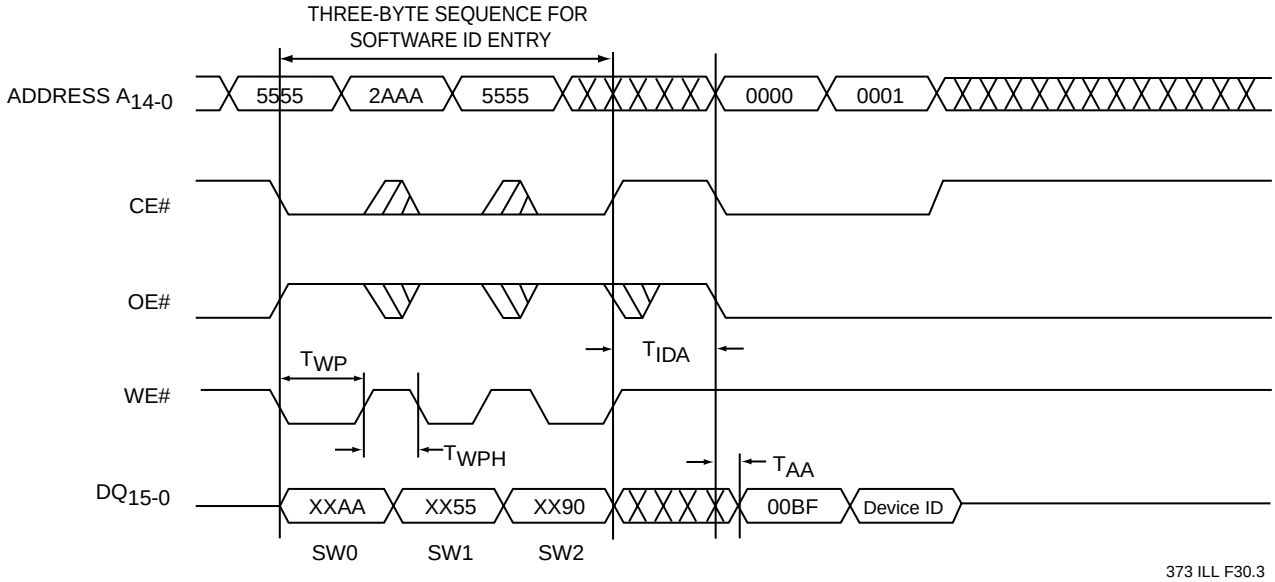
Note: This device also supports CE# controlled Block-Erase operation. The WE# and CE# signals are interchangeable as long as minimum timings are met. (See Table 13)
BA_X = Block Address

FIGURE 11: WE# CONTROLLED BLOCK-ERASE TIMING DIAGRAM



Note: This device also supports CE# controlled Sector-Erase operation. The WE# and CE# signals are interchangeable as long as minimum timings are met. (See Table 13)
SA_X = Sector Address

FIGURE 12: WE# CONTROLLED SECTOR-ERASE TIMING DIAGRAM



Device ID = 2761H for SST36VF1601 and 2762H for SST36VF1602

FIGURE 13: SOFTWARE ID ENTRY AND READ

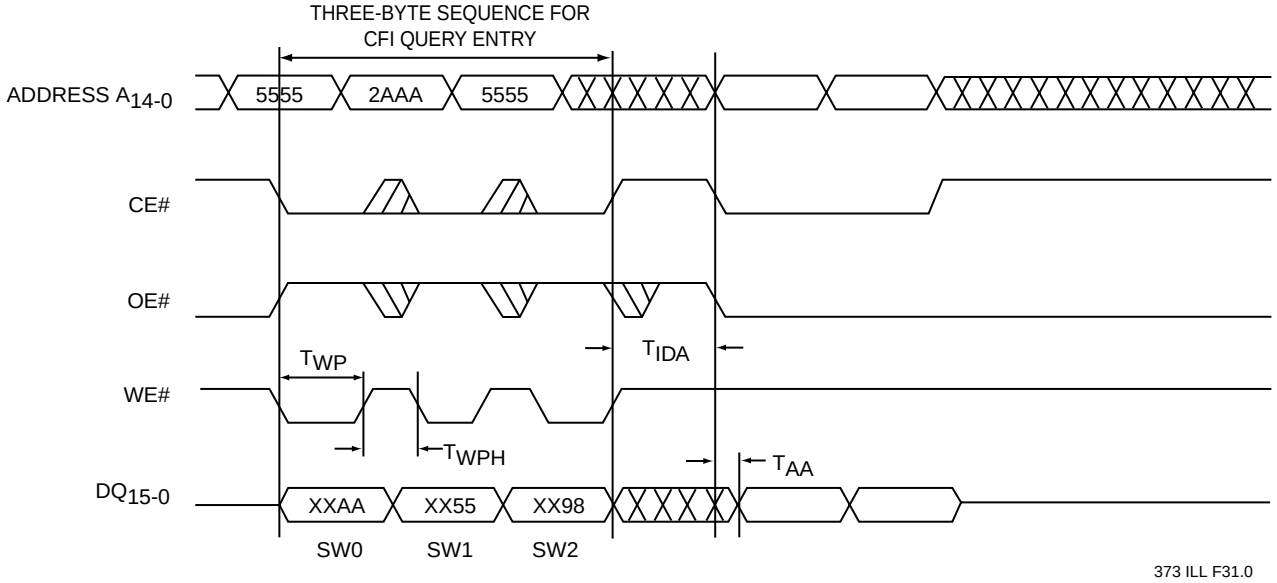


FIGURE 14: CFI ENTRY AND READ

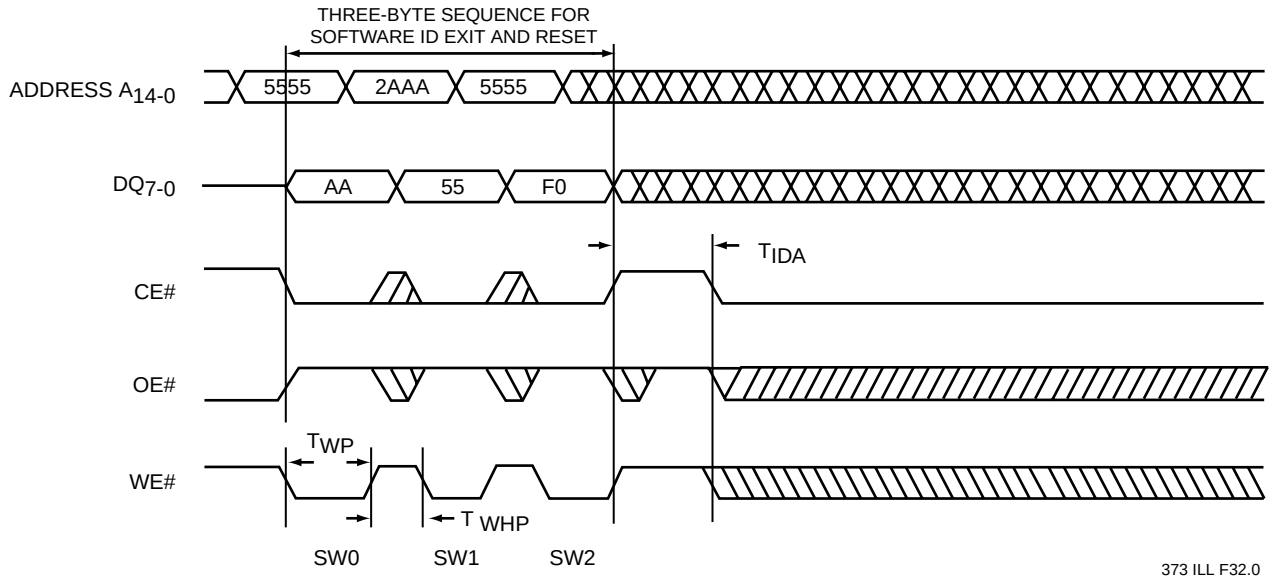


FIGURE 15: SOFTWARE ID EXIT/CFI EXIT

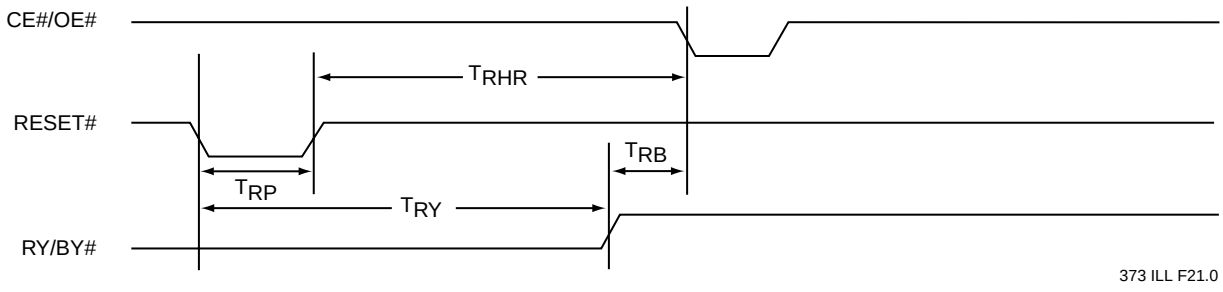
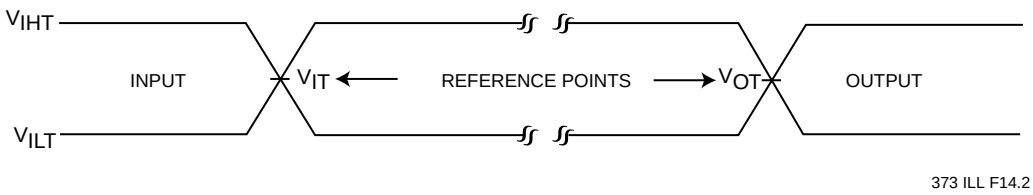


FIGURE 16: RESET# TIMING DIAGRAM



AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT} (0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outputs are V_{IT} (0.5 V_{DD}) and V_{OT} (0.5 V_{DD}). Inputs rise and fall times (10% ↔ 90%) are < 5 ns.

Note: V_{IT}–V_{INPUT} Test
V_{OT}–V_{OUTPUT} Test
V_{IHT}–V_{INPUT} HIGH Test
V_{ILT}–V_{INPUT} LOW Test

FIGURE 17: AC INPUT/OUTPUT REFERENCE WAVEFORMS

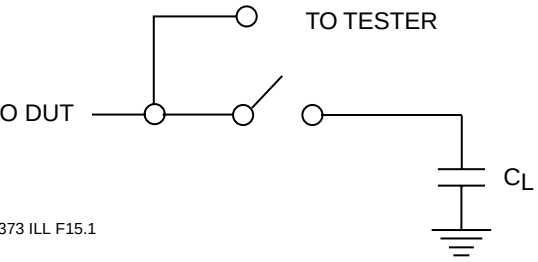


FIGURE 18: A TEST LOAD EXAMPLE

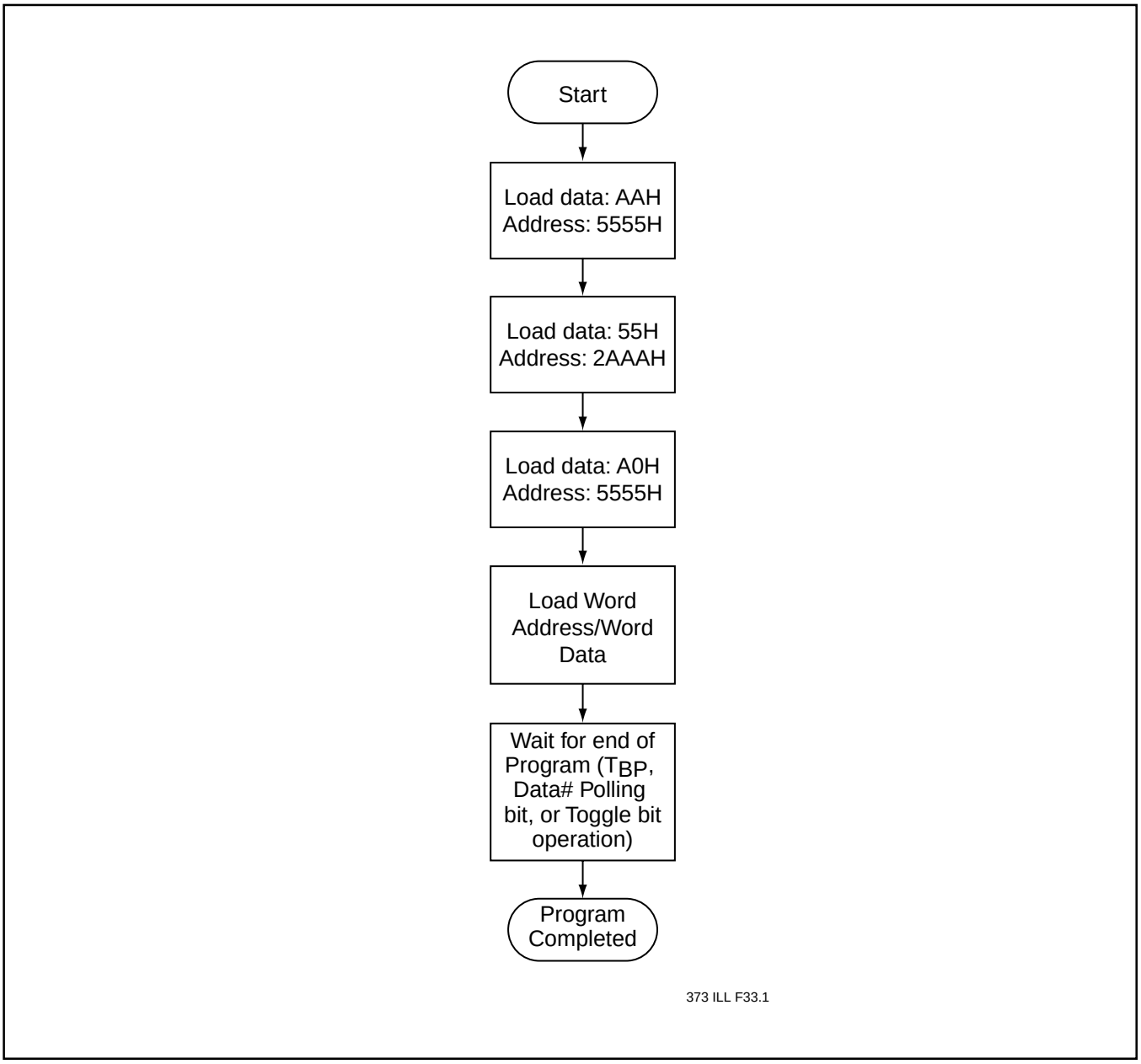


FIGURE 19: WORD-PROGRAM ALGORITHM

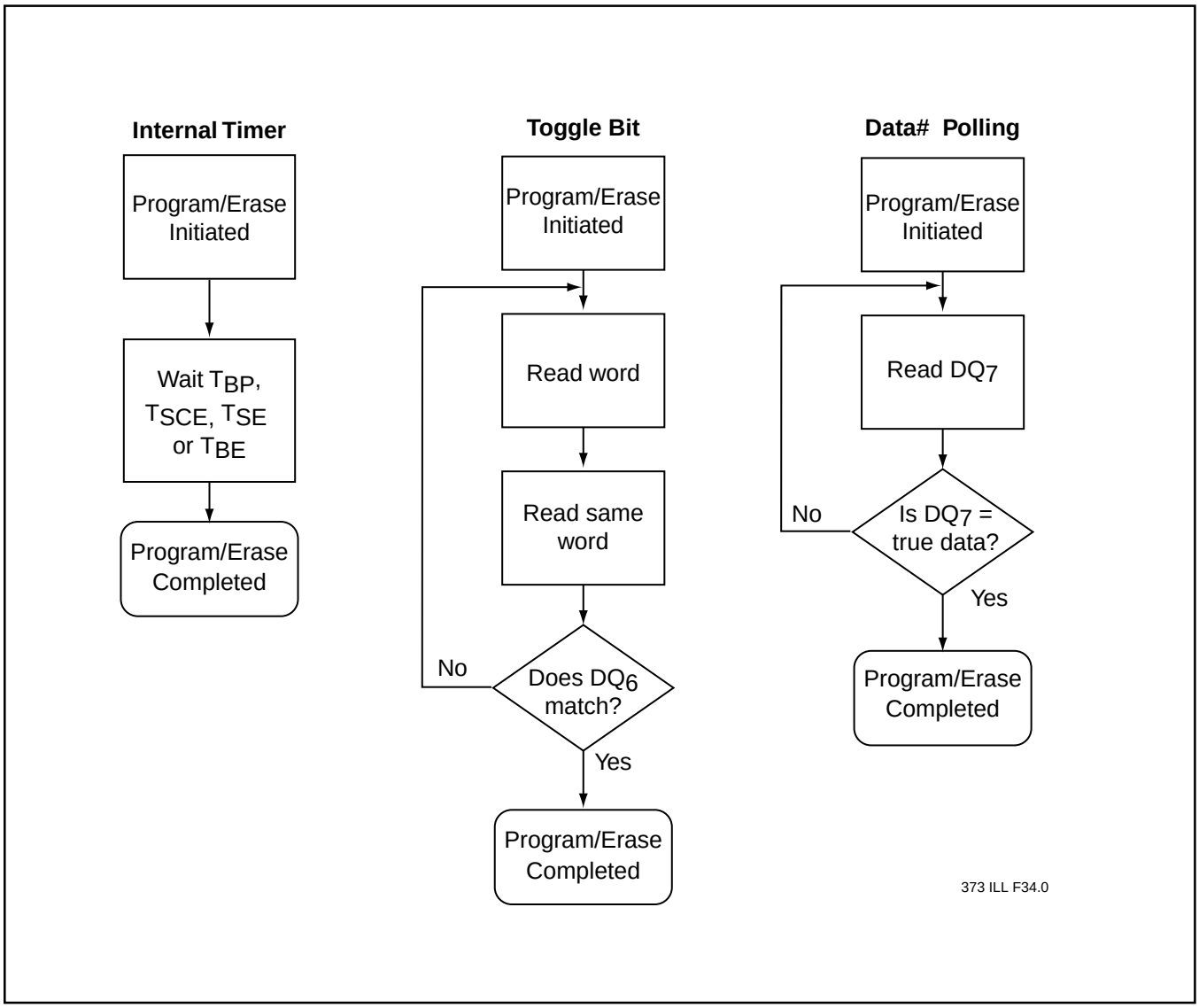


FIGURE 20: WAIT OPTIONS

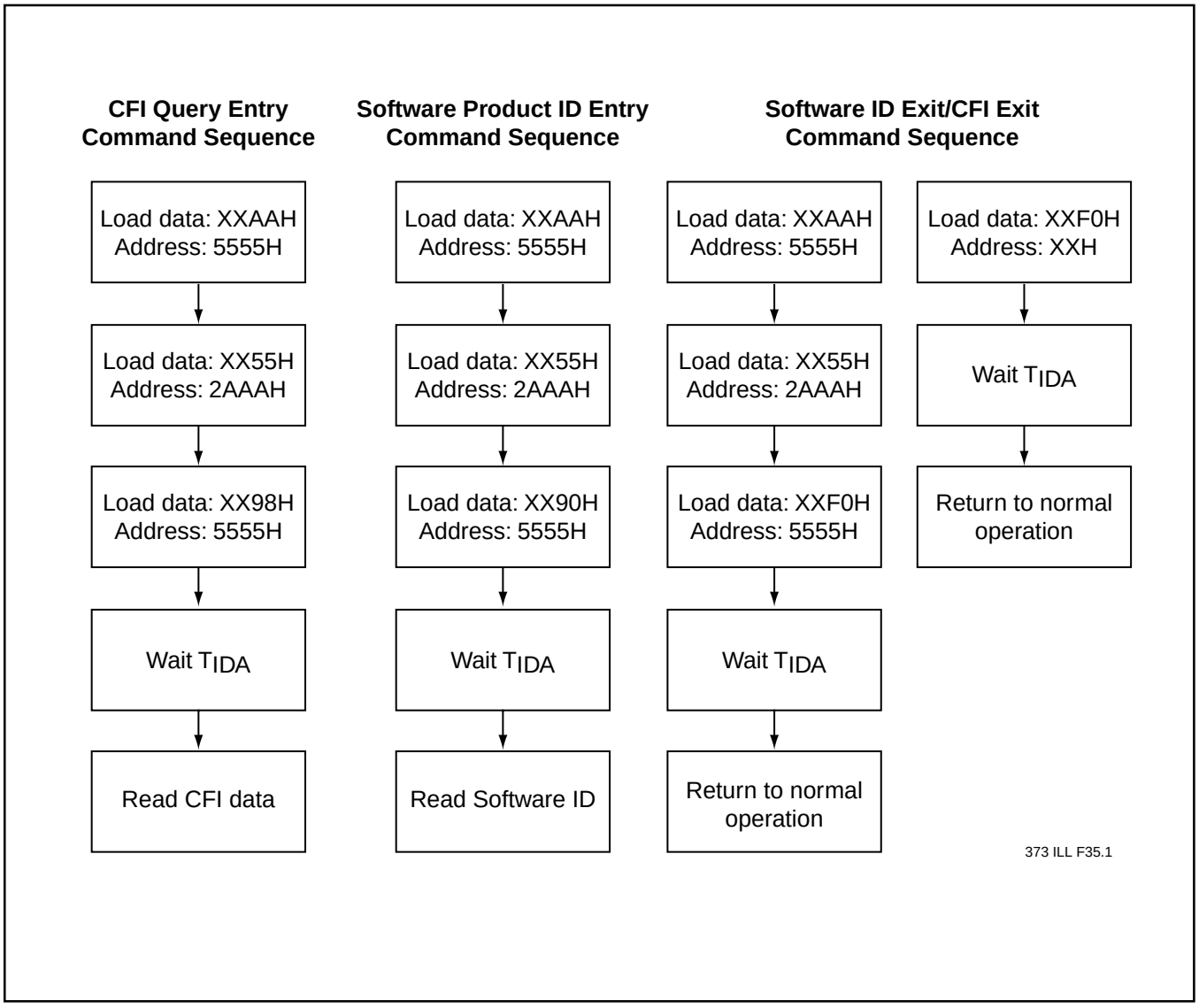


FIGURE 21: SOFTWARE PRODUCT ID/CFI COMMAND FLOWCHARTS

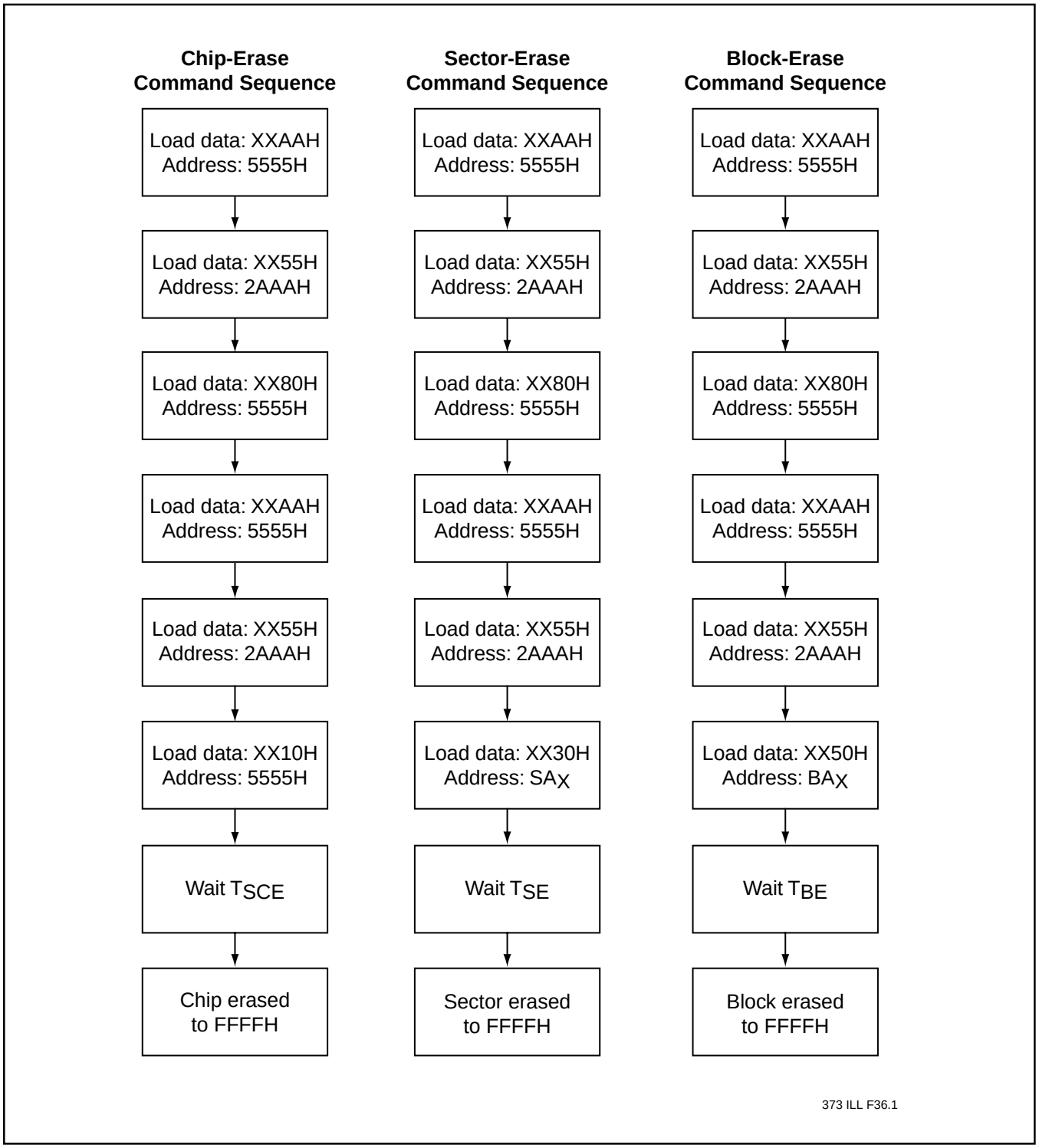
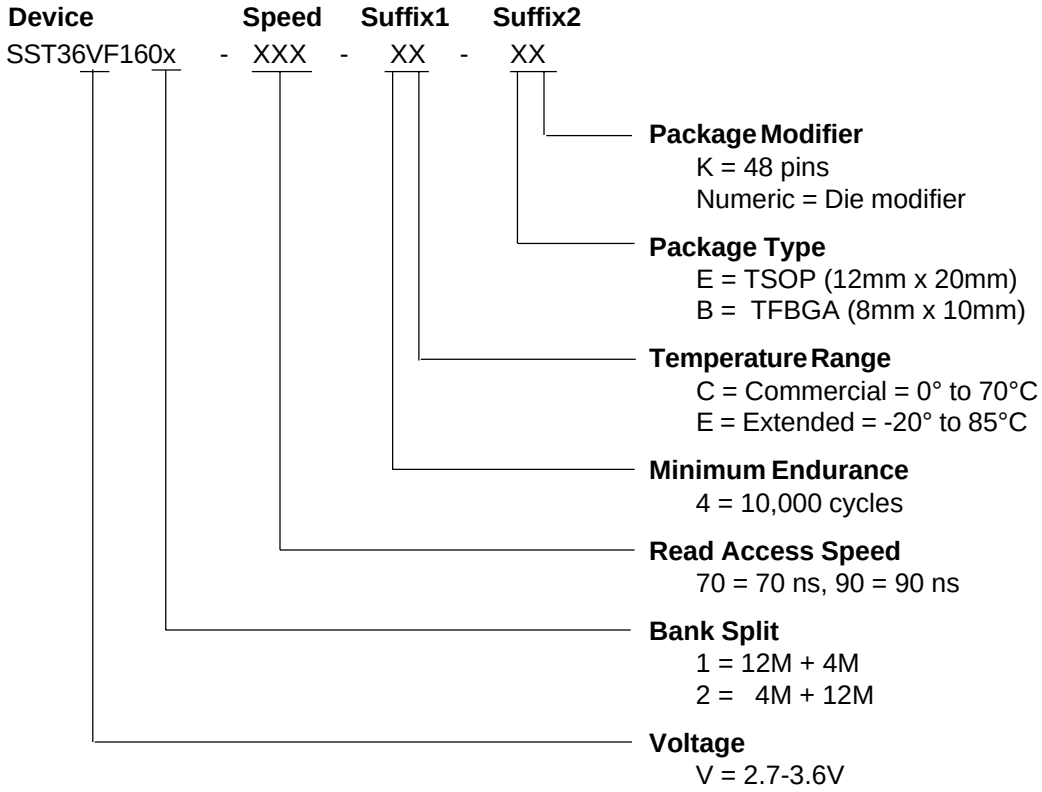


FIGURE 22: ERASE COMMAND SEQUENCE

Advance Information

PRODUCT ORDERING INFORMATION



SST36VF1601 Valid combinations

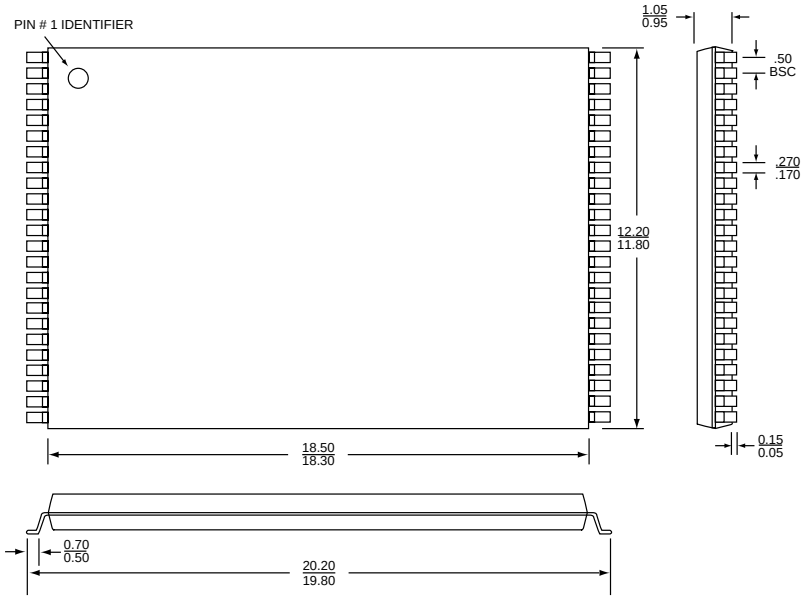
SST36VF1601-70-4C-EK	SST36VF1601-70-4C-BK
SST36VF1601-90-4C-EK	SST36VF1601-90-4C-BK
SST36VF1601-70-4E-EK	SST36VF1601-70-4E-BK
SST36VF1601-90-4E-EK	SST36VF1601-90-4E-BK

SST36VF1602 Valid combinations

SST36VF1602-70-4C-EK	SST36VF1602-70-4C-BK
SST36VF1602-90-4C-EK	SST36VF1602-90-4C-BK
SST36VF1602-70-4E-EK	SST36VF1602-70-4E-BK
SST36VF1602-90-4E-EK	SST36VF1602-90-4E-BK

Example: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

PACKAGING DIAGRAMS

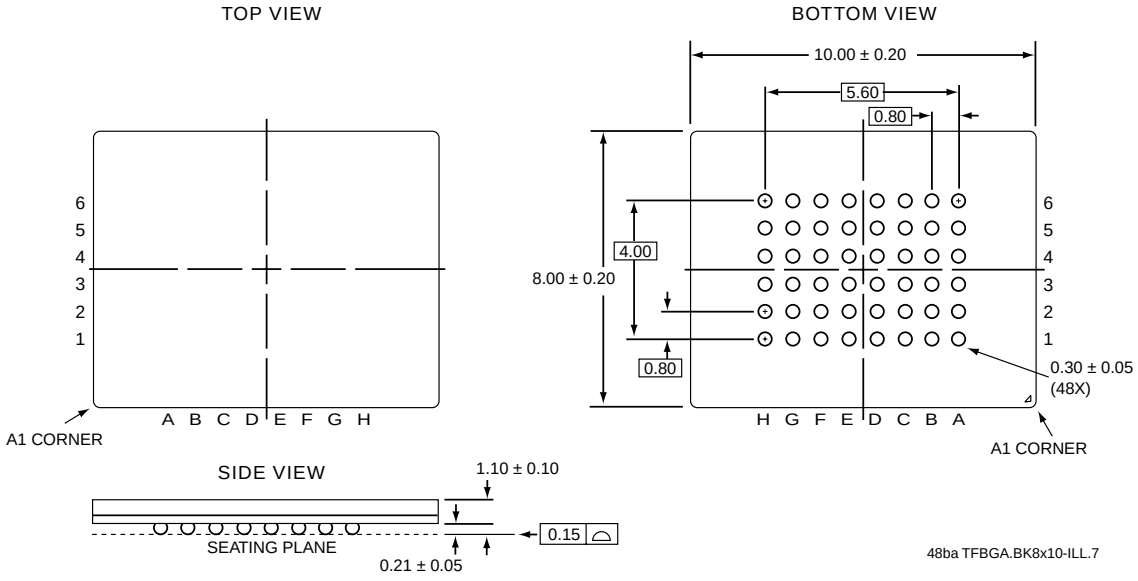


Note: 1. Complies with JEDEC publication 95 MO-142 DD dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in millimeters (min/max).
3. Coplanarity: 0.1 (±.05) mm.

48.TSOP-EK-ILL.4

48-PIN THIN SMALL OUTLINE PACKAGE (TSOP) 12MM X 20MM

SST PACKAGE CODE: EK



48ba TFBGA.BK8x10-ILL.7

Note: 1. Complies with the general requirements of JEDEC publication 95 MO-210, although some dimensions may be more stringent. (This specific outline variant has not yet been registered)
2. All linear dimensions are in millimeters (min/max).
3. Coplanarity: 0.1 (±.05) mm.

48-BALL THIN PROFILE FINE-PITCH BALL GRID ARRAY (TFBGA) 8MM X 10MM

SST PACKAGE CODE: BK